

isc Silicon NPN Power Transistor

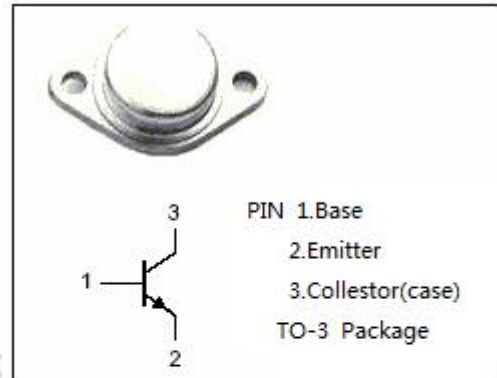
2SC1112

**DESCRIPTION**

- With TO-3 Package
- Wide area of safe operation
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

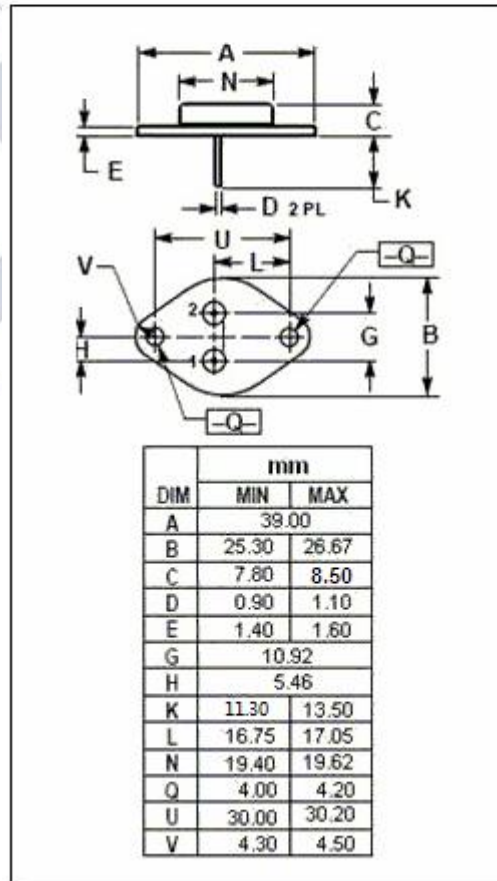
**APPLICATIONS**

- For audio frequency power amplifier applications



**ABSOLUTE MAXIMUM RATINGS (T<sub>a</sub>=25°C)**

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	160	V
V <sub>CEO</sub>	Collector-Emitter Voltage	100	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current-Continuous	6	A
P <sub>C</sub>	Collector Power Dissipation	50	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C



**isc Silicon NPN Power Transistor****2SC1112****ELECTRICAL CHARACTERISTICS****T<sub>c</sub>=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 0.5A			2.0	V
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA; I <sub>B</sub> = 0	100			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1mA; I <sub>C</sub> = 0	5			V
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 3.0A; V <sub>CE</sub> = 4V	30		150	
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 12V; f <sub>test</sub> = 1MHz	10			MHz

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